Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

MCH3477

Power MOSFET
20V, 38mΩ, 4.5A, Single N-Channel

ON Semiconductor®

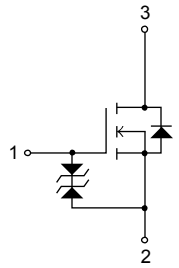
www.onsemi.com

V_{DSS}	R_{DS}(on) Max	I_D Max
20V	38 mΩ@4.5V	4.5A
	61 mΩ@2.5V	
	99 mΩ@1.8V	

Features

- High Speed Switching
- 1.8V Drive
- ESD Diode-Protected Gate
- Low On-Resistance
- Pb-Free, Halogen Free and RoHS Compliance

Electrical Connection
N-Channel



1 : Gate
2 : Source
3 : Drain

Specifications

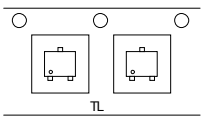
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Value	Unit
Drain to Source Voltage	V_{DSS}	20	V
Gate to Source Voltage	V_{GSS}	±12	V
Drain Current (DC)	I_D	4.5	A
Drain Current (Pulse) PW≤10μs, duty cycle≤1%	I_{DP}	18	A
Power Dissipation When mounted on ceramic substrate (900mm²×0.8mm)	P_D	1.0	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

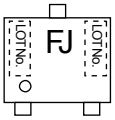
Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm²×0.8mm)	$R_{\theta JA}$	125	°C/W

Packing Type:TL



Marking



Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

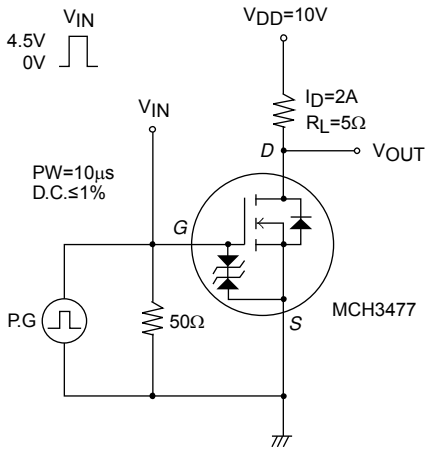
ORDERING INFORMATION
See detailed ordering and shipping information on page 5 of this data sheet.

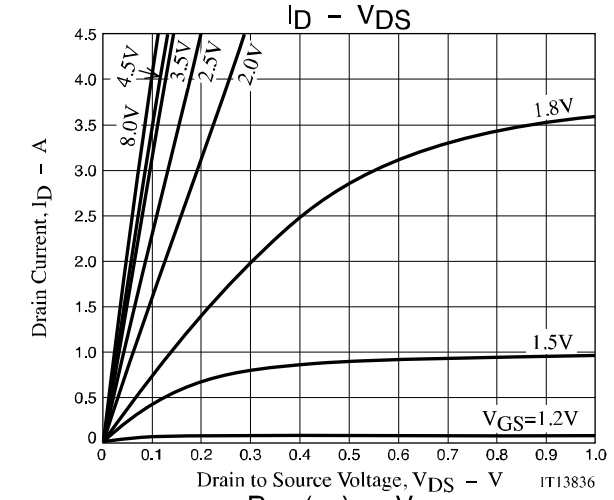
Electrical Characteristics at Ta = 25°C

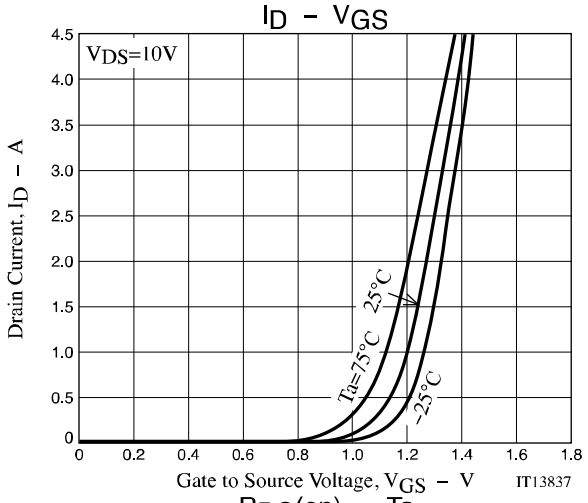
Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0V			1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Gate Threshold Voltage	$V_{GS}(th)$	V_{DS}=10V, I_D=1mA	0.4		1.3	V
Forward Transconductance	g_{FS}	V_{DS}=10V, I_D=2A	2.0	3.4		S
Static Drain to Source On-State Resistance	$R_{DS}(on)1$	I_D=2A, V_{GS}=4.5V		29	38	mΩ
	$R_{DS}(on)2$	I_D=1A, V_{GS}=2.5V		43	61	mΩ
	$R_{DS}(on)3$	I_D=0.5A, V_{GS}=1.8V		69	99	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		410		pF
Output Capacitance	Coss			84		pF
Reverse Transfer Capacitance	Crss			59		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		7.5		ns
Rise Time	t_r			26		ns
Turn-OFF Delay Time	$t_d(off)$			38		ns
Fall Time	t_f			32		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=4.5V, I_D=4.5A		5.1		nC
Gate to Source Charge	Qgs			0.7		nC
Gate to Drain “Miller” Charge	Qgd			1.7		nC
Forward Diode Voltage	V_{SD}	I_S=4.5A, V_{GS}=0V		0.78	1.2	V

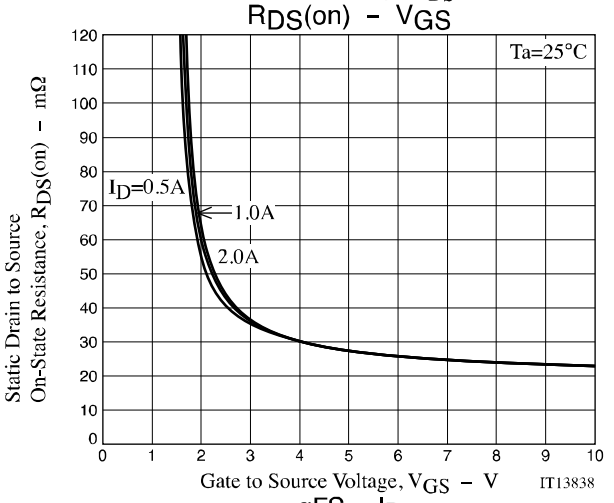
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

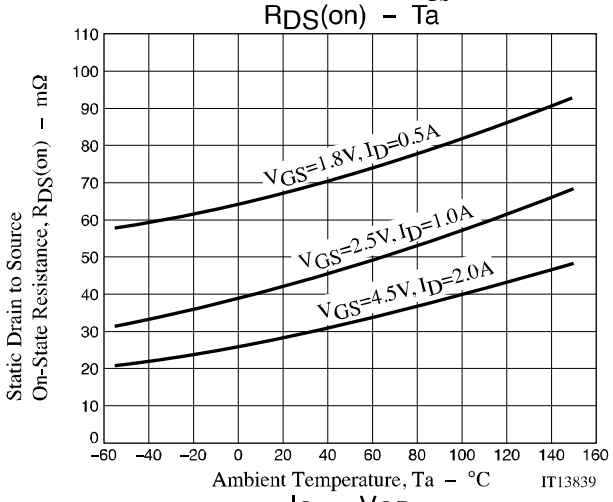
Switching Time Test Circuit

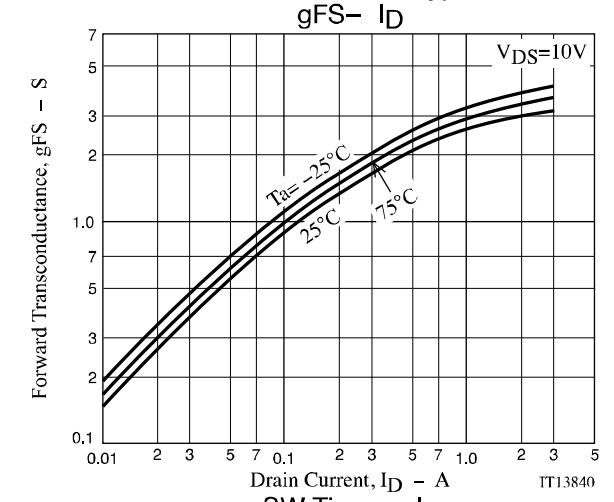


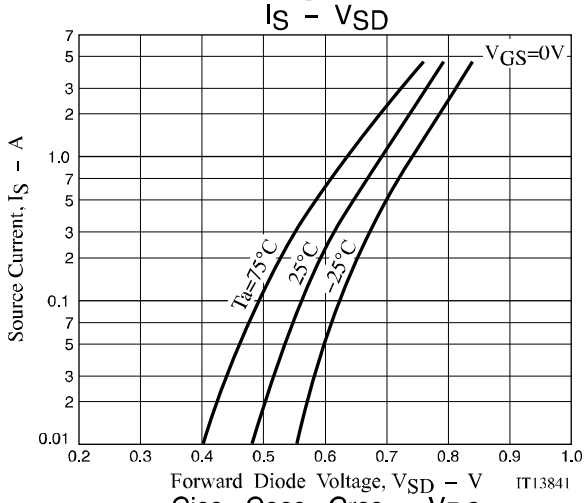

ID – VDS
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT13836
4.5V
3.5V
2.5V
2.0V
8.0V
1.8V
1.5V
VGS=1.2V

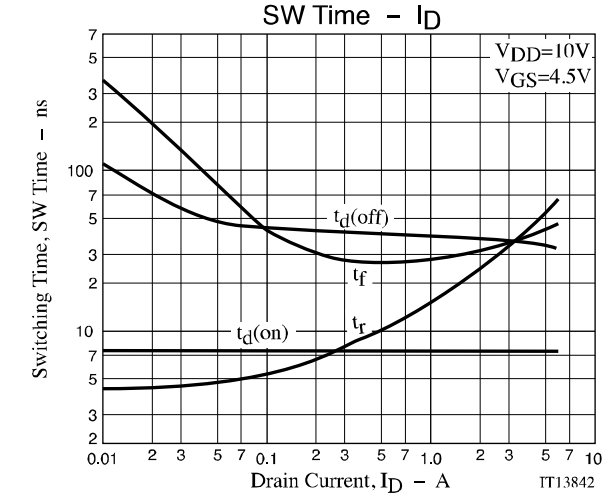

ID – VGS
VDS=10V
Drain Current, ID – A
Gate to Source Voltage, VGS – V
IT13837
25°C
Ta=75°C
–25°C

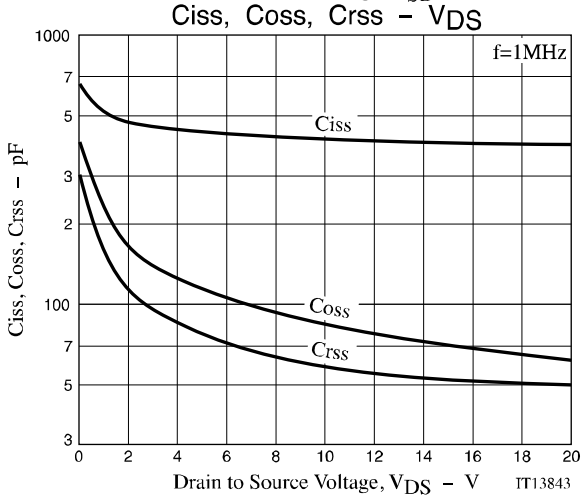

RDS(on) – VGS
Ta=25°C
Static Drain to Source
On-State Resistance, RDS(on) – mΩ
Gate to Source Voltage, VGS – V
IT13838
ID=0.5A
1.0A
2.0A

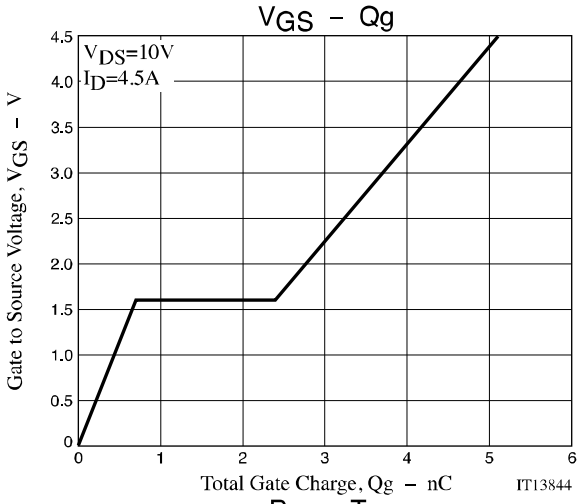

RDS(on) – Ta
Static Drain to Source
On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT13839
VGS=1.8V, ID=0.5A
VGS=2.5V, ID=1.0A
VGS=4.5V, ID=2.0A

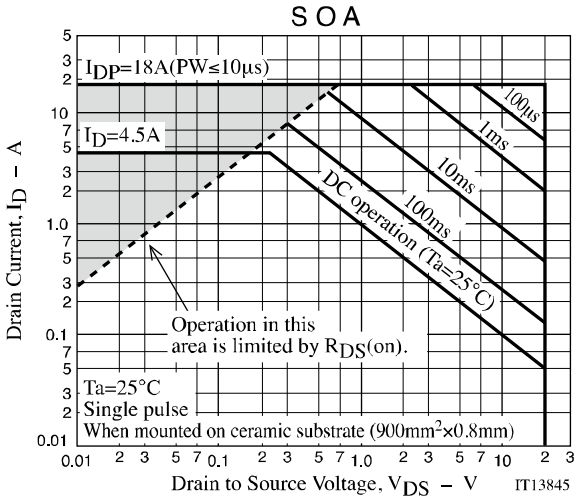

gFS– ID
VDS=10V
Forward Transconductance, gFS – S
Drain Current, ID – A
IT13840
Ta=–25°C
25°C
75°C

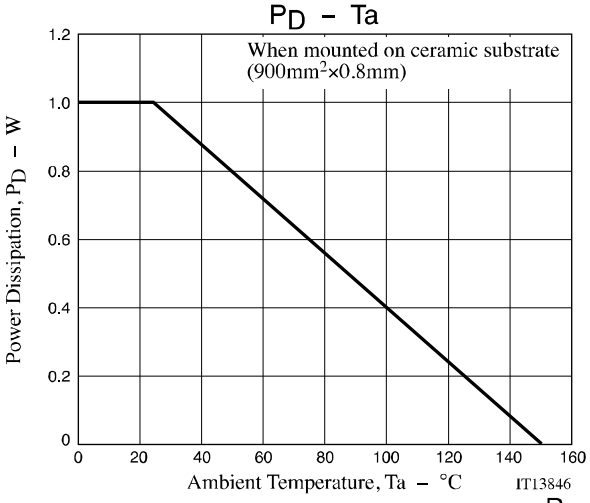

IS – VSD
VGS=0V
Source Current, IS – A
Forward Diode Voltage, VSD – V
IT13841
Ta=75°C
25°C
–25°C

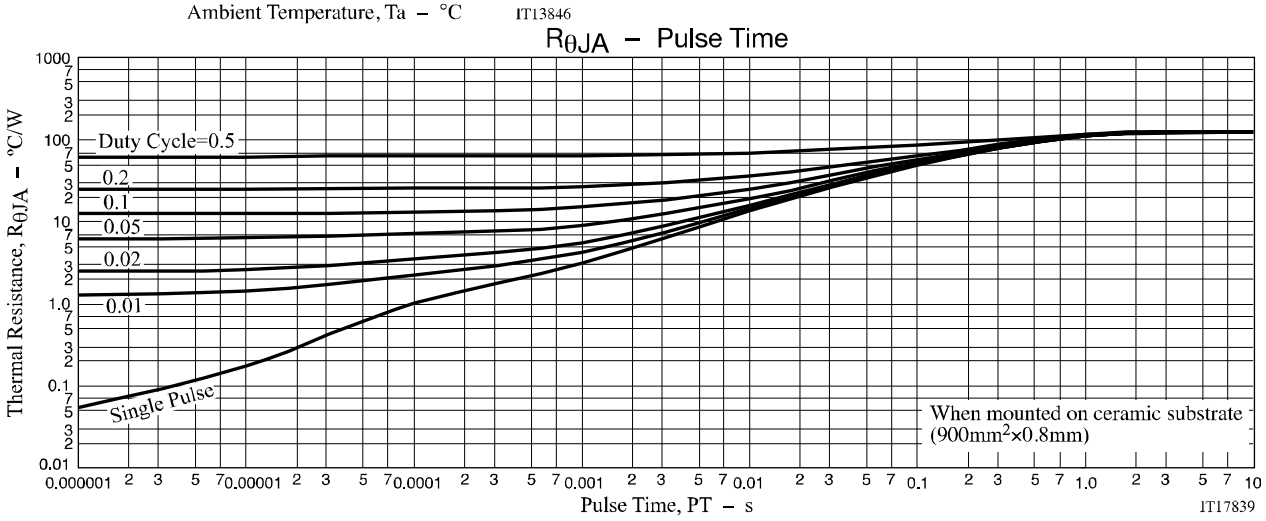

SW Time – ID
VDD=10V
VGS=4.5V
Switching Time, SW Time – ns
Drain Current, ID – A
IT13842
td(off)
tf
tr
td(on)


Ciss, Coss, Crss – VDS
f=1MHz
Ciss, Coss, Crss – pF
Drain to Source Voltage, VDS – V
IT13843
Ciss
Coss
Crss


VGS – Qg
VDS=10V
ID=4.5A
Gate to Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT13844


S O A
IDP=18A(PW≤10μs)
ID=4.5A
100μs
1ms
10ms
100ms
DC operation (Ta=25°C)
Operation in this
area is limited by RDS(on).
Ta=25°C
Single pulse
When mounted on ceramic substrate (900mm2×0.8mm)
Drain Current, ID – A
Drain to Source Voltage, VDS – V
IT13845


PD – Ta
When mounted on ceramic substrate
(900mm2×0.8mm)
Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT13846


RθJA – Pulse Time
Duty Cycle=0.5
0.2
0.1
0.05
0.02
0.01
Single Pulse
When mounted on ceramic substrate
(900mm2×0.8mm)
Thermal Resistance, RθJA – °C/W
Pulse Time, PT – s
IT17839

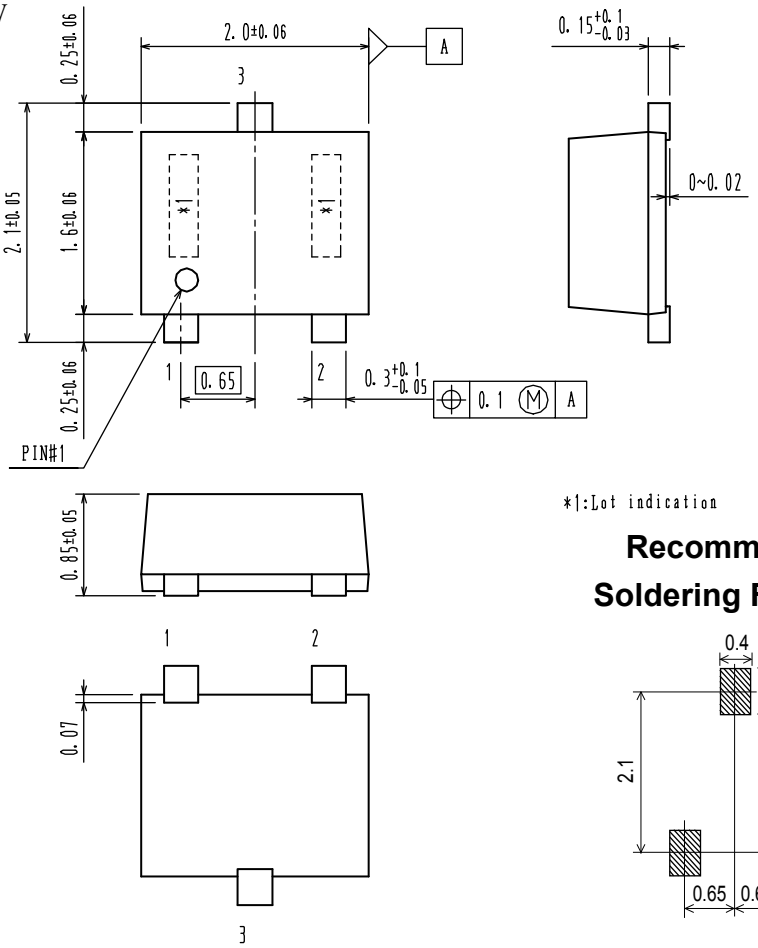
Package Dimensions

MCH3477-TL-H / MCH3477-TL-W

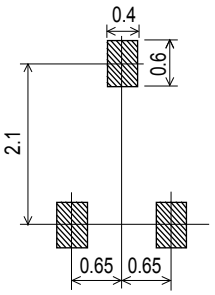
MCPH3
CASE 419AQ
ISSUE O

Unit : mm

1 : Gate
2 : Source
3 : Drain



Recommended Soldering Footprint



ORDERING INFORMATION

Device	Package	Shipping	Note
MCH3477-TL-H	MCPH3 SC-70,SOT-323	3,000 pcs. / reel	Pb-Free and Halogen Free
MCH3477-TL-W			

Note on usage : Since the MCH3477 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.